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Atomic-Scale Defected HfS₂ Nanosheets: A Novel Platform Enhancing Photocatalysis

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Recently, novel 2D materials with fascinating characteristics are extensively applied to design/fabricate high-activity and cost-effective photocatalysts for solar-driven fuels/chemicals generation. Among these 2D materials, HfS₂ nanosheets (NSs) exhibit excellent features of large surface area, short bulk-to-surface distance, alterable band structures, and vast catalytic sites. Despite these features, no realistic experimental works on HfS2-based materials are reported in photocatalysis field. Moreover, it is interesting but challenging to realize atomic-scale engineering of compositions/structures for novel 2D materials and to relate these atomic-scale characteristics with the element/space/time-resolved charge kinetics of 2D materials-based photocatalysts. Herein, for the first time, atomic-scale defected HfS₂ NSs are designed/synthesized. The as-synthesized HfS₂ NSs are combined with various photocatalysts to acquire novel HfS2-TiO2, HfS2-CdS, HfS2-ZnIn2S4, and HfS2-C3N4 composites, respectively. Among them, HfS2-CdS exhibits the highest rate (5971 μ mol g⁻¹ h⁻¹) on hydrogen (H₂) evolution in triethanolamine aqueous solution, together with obviously-enhanced rates on H₂ (2419 μ mol g⁻¹ h⁻¹) and benzaldehyde (5.11 mmol g⁻¹ h⁻¹) evolution in benzyl alcohol aqueous solution. Various state-of-art characterizations reveal the element/space/time-resolved electron/hole kinetics in HfS2-CdS composites, disclosing that these atomic-scale S vacancies temporarily trapping electrons to facilitate spatiotemporal electron-hole separation/transfer. This work paves avenues to atomic-scale design/synthesis of new 2D-materials-based photocatalysts for sunlight utilization.

1. Introduction

Adopting photocatalysis technique to convert renewable solar energy into fuels/chemicals is of great significance to resolve the

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global energy/environmental issues.[1-12] Realistic application of this technique rests with the development of highactivity, stable and cheap photocatalysts. In the past decades, tremendous novel 2D materials have been developed and applied in photocatalysis field due to their distinctive features.[13-27] Among these new 2D materials, HfS2 nanosheets (NSs) stands out owing to the appealing characteristics: 1) controllable thickness and lateral sizes to regulate the electronic band structures for optimizing the light absorption abilities and electron-hole redox capacities; 2) 2D structure benefiting the charge transfer from bulk to surface; 3) abundant undercoordinated catalytic sites on the large surface boosting the redox reactions; 4) high surface area facilitating the combination with all sorts of nanoscale building blocks. Despite these fascinating attributes, up till now, only some theoretical computations of HfS2-based photocatalysts were reported on this field.^[28-31] To the best of our knowledge, no realistic experimental works on HfS2-based materials are reported in photocatalysis field to date.

Regulating the atomic-scale structures/compositions of novel 2D materials

to optimize the physicochemical features is of central importance to realize the outstanding photocatalytic performances in key reactions. Especially, it is highly desirable to engineer the atomic-level structures of 2D materials, such as introducing atomic-scale cation and/or anion vacancies, for achieving efficient kinetics of light-excited electrons/holes in photocatalysts.[32-38] These atomic-level defects with positive/negative charges can serve as the efficient trapping sites to temporarily accommodate the photo-generated electrons/holes only, thus achieving effective dissociation/migration of electronhole pairs. It is interesting but also challenging to reveal the roles of these atomic-level defects for regulating the charge dynamics. Thus, using state-of-art characterizations to disclose the element/space/time-resolved electrons/holes dynamics in photocatalysts is desirable. More importantly, relating the above-disclosed charge kinetics with the atomic-scale structures/compositions in photocatalysts is pivotal to direct atomic-level design/fabrication of high-activity photocatalysts.

Unfortunately, this sort of research is also rarely covered in photocatalysis.

Herein, we for the first time design and fabricate the atomicscale defected HfS₂ NSs using a sonication route. The asfabricated atomic-scale defected HfS₂ NSs were coupled with four different photocatalysts to fabricate the new HfS₂-TiO₂, HfS₂-CdS, HfS₂-ZnIn₂S₄, and HfS₂-C₃N₄ composites, respectively. All four composites exhibit the apparent elevation of photocatalytic H₂ generation in triethanolamine (TEOA) aqueous solution, suggesting the universal enhancement effect by HfS₂ NSs for photocatalytic H₂ evolution. The highest photocatalytic H₂ evolution rate (5971 μ mol g⁻¹ h⁻¹) is observed on the optimized HfS₂-CdS. The optimized HfS₂-CdS also displays obviously-raised evolution rates of H_2 (2419 µmol g⁻¹ h⁻¹) and benzaldehyde (5.11 mmol $g^{-1} h^{-1}$) in benzyl alcohol aqueous solution. Indeed, the obtained results strongly confirm the tremendous impact of the heterojunction photocatalytic systems, which have been adopted to accelerate the migration of photogenerated electrons and holes to various counterparts for reduction and oxidation reactions and to prolong their lifetimes.[39] Such phenomenon could be revealed by application of various in situ characterization analysis, such as in situ X-Ray photoelectron spectroscopy, in situ atomic force microscopy-Kelvin probe force microscopy, and ultrafast transient absorption spectroscopy. Actually, the atomic-scale S vacancies of HfS₂ NSs are found to temporarily attract photo-excited electrons, thus resulting in efficient spatiotemporal dissociation/migration of photo-excited electronhole pairs in 40.0H. This Research demonstrates the great importance of developing distinctive 2D materials with atomic-scale defects for efficient solar-to-chemicals conversion.

2. Results and Discussion

2.1. Structures and Compositions

First, we synthesized HfS₂ nanosheets (NSs) via exfoliating bulk HfS₂ in ethanol using the sonication route in the ice bath. Then, the sonicated HfS2 suspensions were centrifuged to remove the thick/large HfS2 and acquire the thin/small HfS₂ NSs dispersed in ethanol. The X-ray diffraction (XRD) pattern of bulk HfS₂ (Figure S1, Supporting Information) exhibits the hexagonal phase HfS₂. The high-angle annular dark field-scanning transmission electron microscopy (HAADF-STEM) image (Figure S2a, Supporting Information) of bulk HfS₂ indicates the lattice spacing distances of 3.1 and 3.1 Å with an angle of 60° , corresponding to the (100) and (010) facet of hexagonal HfS2. The atomic-resolution differential phase contrast (DPC)-STEM image (Figure S2b, Supporting Information) and corresponding line analysis of bulk HfS₂ (Figure S2c, Supporting Information) disclose the absence of any S vacancy in bulk HfS₂. The HAADF-STEM image of HfS₂ NSs (Figure S3a, Supporting Information) exhibits the 2D NSs morphology with the lateral sizes of \approx 300–400 nm for HfS₂ NSs. The energy-dispersive X-Ray (EDX) spectroscopy of HfS2 NSs in Figure S3b (Supporting Information) indicates the existence of Hf and S elements. Furthermore, the HAADF-STEM image (Figure S4a, Supporting Information) and corresponding elemental mapping images of Hf (Figure S4b, Supporting Information) and S (Figure S4c, Supporting Information) for HfS2 NSs further confirm the successful synthesis of HfS₂ NSs. Moreover, the AFM image (Figure S5a, Supporting Information) and corresponding height profile (Figure S5b, Supporting Information) reveal that the thickness of HfS₂ NSs is \approx 30–40 nm. The atomic-resolution HAADF-STEM image (Figure 1a) shows the lattice distance values of 3.1 and 3.1 Å with an angle of 60°, corresponding to the (010) and (100) facets of hexagonal HfS2. The Atomic-Resolution DPC-STEM image (Figure 1b) and corresponding line analyses (Figure 1c-e) together confirm the existence of S vacancies (V_s) in HfS₂ NSs. These results confirm the successful synthesis of atomic-scale defected HfS2 NSs. These S vacancies can possibly enhance the interaction between HfS₂ NSs and photocatalyst loaded on the surface. Subsequently, CdS nanoparticles (NPs) were synthesized by a hydrothermal approach. The TEM image of as-synthesized CdS NPs (Figure S6a, Supporting Information), as abbreviated as 0.0H, shows the aggregation of CdS NPs with sizes of $\approx 10-30$ nm. The high-resolution TEM (HRTEM) image (Figure S6b, Supporting Information) of 0.0H exhibits two lattice spacing values of 3.4 and 3.4 Å with an angle of 109.5°, corresponding to the (111) and (1-1-1) facets of cubic-phase CdS. The EDX spectrum of 0.0H in Figure S6c (Supporting Information) shows the existence of Cd and S elements. The HAADF-STEM image (Figure S6d, Supporting Information) and the corresponding elemental mapping images of Cd (Figure S6e, Supporting Information) and S (Figure S6f, Supporting Information) also confirm the successful synthesis of CdS NPs.^[40] Subsequently, a range of HfS₂ coupled CdS (HfS₂/CdS) composite photocatalysts were fabricated by a simple physical mixing at room temperature. Specifically, 50 mg of the as-synthesized CdS NPs were combined with 20.0, 30.0, 40.0, and 50.0 mL of HfS₂ NSs ethanol solutions, respectively. The as-synthesized samples were labeled as 20.0H, 30.0H, 40.0H, and 50.0H, respectively. The XRD patterns of 0.0H and 40.0H are shown in Figure S7 (Supporting Information). No obvious change of the peak positions and intensities for CdS phase is found since the physical mixing of HfS₂ NSs and CdS NPs at room temperature can't affect the crystal structure of CdS phase. The existence of small XRD peaks assigned to HfS₂ phase is observed in the XRD pattern of 40.0H, also suggesting the combination of HfS₂ with CdS in 40.0H. TEM image of 40.0H (Figure 2a) indicates the dispersion of CdS NPs on the surface of HfS₂ NSs. High-Resolution HAADF-STEM image of 40.0H (Figure 2b) shows the lattice spacing values of 3.1 and 2.1 Å with an angle of 109.9° , ascribed to the (100) and (-112) facets of hexagonal HfS₂ NSs, respectively. Figure 2b also shows the lattice spacing values of 3.4 and 3.4 Å with an angle of 70.5°, attributed to the (111) and (11-1) planes of cubic CdS, respectively. The EDX spectrum (Figure 2c) further confirms the existence of Cd, S, and Hf elements for 40.0H. The HAADF-STEM image (Figure 2d) and the corresponding elemental mapping images of Hf, Cd, and S elements for 40.0H (Figure 2e-g) also confirm the successful loading of CdS NPs on surface of HfS₂ NSs. The high-resolution XPS spectra of 40.0H (Figure S8, Supporting Information) further confirm the successful combination of CdS NPs with HfS₂ NSs in 40.0H.

The microstructure and pore size distribution of 0.0H and 40.0H were also studied by the nitrogen (N_2) sorption analysis. The results in Figure S9 (Supporting Information) indicate the



Figure 1. a) Atomic-Resolution HAADF-STEM image, b) Atomic-Resolution DPC-STEM image, and c-e) corresponding line analyses for S vacancies in HfS₂ NSs.

overall down shift of the whole sorption isotherm for 40.0H, compared with that of 0.0H. Also, the pore size distribution curve of 40.0H is lower than that of 0.0H. Accordingly, Table S1 (Supporting Information) exhibits the reduced surface area (25.88 m² g⁻¹) and pore volume (0.155 cm³ g⁻¹) of 40.0H, in contrast with those of 0.0H (50.00 m² g⁻¹ and 0.284 cm³ g⁻¹). This is because that the larger sizes of defected HfS₂ NSs (averaged thickness of \approx 30–40 nm and lateral sizes of \approx 300–400 nm) compared to those of CdS NPs (sizes of \approx 10–30 nm) lead to lower surface areas and pore volumes arising from the stacking of the bigger-sized HfS₂ NSs.

2.2. Excellent Performances on ${\rm H_2}$ and Benzaldehyde Evolution

The photocatalytic H_2 evolution activities of all the samples (0.0H, 20.0H, 30.0H, 40.0H, and 50.0H) were examined using

TEOA, benzyl alcohol (BA) and benzylamine as the substrates, respectively. As displayed in Figure 3a, 0.0H (bare CdS) only exhibits a photocatalytic H₂ evolution rate of 574 μ mol g⁻¹ h⁻¹, ascribing to rapid electron-hole recombination. In contrast, all the HfS₂/CdS composites (20.0H, 30.0H, 40.0H, and 50.0H) exhibit obviously-raised photocatalytic H₂ evolution rates of 1034, 2316, 5971, and 2394 $\mu mol~g^{-1}~h^{-1},$ respectively, compared to CdS alone. Especially, 40.0H exhibits the highest photocatalytic H_2 evolution rate of 5971 µmol g⁻¹ h⁻¹, due to the excellent balance of charge kinetics and light harvesting. Since 40.0H exhibits the highest photocatalytic H₂ evolution rate of 5971 µmol g^{-1} h⁻¹, we further tested the photocatalytic H₂ evolution rates of 40.0H using BA and benzylamine as the substrates, respectively. As shown in Figure 3b, 40.0H shows the obviously-raised photocatalytic H₂ evolution rates of 2419 and 2452 μ mol g⁻¹ h⁻¹ in BA and benzylamine aqueous solution, respectively. In contrast, 0.0H only exhibits the photocatalytic H₂ evolution rates







Figure 2. a) TEM image, b) high-resolution HAADF-STEM image, and c) EDX spectrum of 40.0H. d) HAADF-STEM image and the corresponding elemental mapping images of e) Hf, f) Cd, and g) S elements for 40.0H.

of 957 and 983 μ mol g⁻¹ h⁻¹ in BA and benzylamine aqueous solution, respectively. These results show the enhancement factors of \approx 253% and \approx 249% in H₂ evolution rates for 40.0H in BA and benzylamine aqueous solution, respectively. H₂ evolution rate of 40.0H was compared with reported studies and the results are reported in Table S2 (Supporting Information). Our work shows one of the highest photocatalytic H₂ evolution rates, suggesting excellent photocatalytic performance for 40.0H. Furthermore, 40.0H exhibits the photocatalytic H₂ evolution rates of 607 and 481 µmol g⁻¹ h⁻¹ using 365 and 420 nm light emitting diode (LED) irradiation, respectively (Figure S10, Supporting Information). In addition, photocatalytic H₂ evolution over HfS₂ NSs was investigated in various reaction conditions. As shown in Figure 3b, HfS₂ NSs exhibit the low photocatalytic H₂ evolution activities in TEOA, BA, and benzylamine aqueous solution, respectively. Thus, HfS₂ NSs only contribute to a small section in the photocatalytic activities of 40.0H in various reaction conditions (Figure 3b). Furthermore, the stability of photocatalytic H₂ evolution on 40.0H was also tested. It can be observed that 40.0H reserves the excellent stability for photocatalytic H₂ evolution in 12 h reaction (Figure S11, Supporting Information). Interestingly, compared to H₂ evolution amounts in the first cycle, the H₂ evolution amounts decrease in the second and third cycles, but increase again in the fourth cycle. These slight changes of H_2 evolution arises from several possible factors, such as environmental temperature, agglomeration of photocatalyst in reactor, and effective interaction between HfS2 NSs and CdS NPs in reactor. The reacted 40.0H (annotated as 40.0H-R), shows no obvious difference in the morphology (Figure S12a-c, Supporting Information) and chemical compositions (Figure S12d, Supporting Information) compared to those before the reaction (Figure 2a,c).

On the other hand, the photocatalytic benzaldehyde (BAD) evolution rates on 0.0H and 40.0H were also studied. As displayed in Figure S13a,b (Supporting Information), 0.0H exhibits the conversion of 49.70% and selectivity of 14.31% in 12 h reaction, leading to the averaged BAD evolution rate of 3.32 mmol g⁻¹ h⁻¹. As a contrast, 40.0H shows the conversion of 54.61% and selectivity of 20.04% in 12 h reaction, corresponding to the averaged BAD evolution rate of 5.11 mmol g⁻¹ h⁻¹. Therefore, 40.0H exhibits ≈154% times higher averaged BAD evolution rate in 12 h reaction, compared with that of 0.0H. All these results confirm the obvious rise on photocatalytic co-generation of H₂ and BAD for 40.0H, compared to those of 0.0H. Additionally, the possible by-products are benzoic acid and benzyl benzoate.^[41-43]

2.3. Light Absorption and Band Structures

To investigate the reason on the simultaneous raises on H_2 and BAD evolution of 40.0H, various advanced characterizations were adopted to study the light absorption, charge kinetics, and surface redox reactions of 40.0H. First, we used UV–vis diffuse reflectance spectroscopy to explore the light absorption properties of 0.0H, 40.0H, HfS₂ NSs, and bulk HfS₂. The colors of these samples are shown in Figure S14 (Supporting Information). The corresponding results (Figure S14, Supporting Information) exhibit that the absorption edge is red-shifted from 558.6 nm for 0.0H to 574.3 nm for 40.0H. This indicates the increased light responsive range for 40.0H compared to that of 0.0H, due to the introduction of HfS₂ NSs with a much smaller bandgap (1.42 eV) than that of CdS (2.22 eV). After the combination with HfS₂ NSs, 40.0H shows an obviously reduced light absorption in the

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a 7000 b HfS₂ NSs 5971 6000 H_2 evolution rate $(\mu mol \ h^{\text{-1}}g^{\text{-1}})$ $\rm H_2$ evolution rate (µmol $g^{-1}h^{-1})$ 5971 0.0H 6000 40.0H 5000 5000 4000 4000 3000 3000 2419 2452 2316 2000 2000 egligible 1034 957 1000 1000 574 0 40Cat Nolight 30,011 10.011 50.011 0.011 20,011 TEOA **Benzyl** alcohol Benzylamine d e С Hf 4f of 40.0H Cd 3d of 40.0H S 2p of 40.0H Cd 3d 5/2 Hf 4f7/2 S 2p3/2 405.1 eV Hf 4f5/2 17.2 e Cd 3d3/2 161.7 S 2p_{1/2} 18.9 eV 411.8 eV 163 eV Intensity (a.u.) Intensity (a.u.) Intensity (a.u.) light on light on light on Cd 3d5/2 Hf 4f_{7/2} 404.8 eV Hf 4f5/2 S 2p_{3/2} Cd 3d 17.1 eV 18.8 eV S 2p_{1/2} 161.6 eV 411.6 eV 162.8 eV light off light off light off 414 16 17 18 19 20 402 404 406 408 410 412 416 15 21 161 162 163 164 160 165 **Binding energy (eV)** Binding energy (eV) **Binding energy (eV) g** 1.2 V 40.0H (Dark) 40.0H (Light Potential (V) otential (V) Potential (V) otential (V 1.1 V 1.15 1.1 V 0.0 0.2 0.6 1.2 0.4 0.8 1.0 0.2 0.6 1.0 12 0.0 0.4 0.8 Distance (µm) 0.0 Distance (µm) 1.3 Distance (µm) Distance (um)

Figure 3. a) Photocatalytic H₂ evolution rates of 0.0H, 20.0H, 30.0H, 40.0H, and 50.0H in \approx 17 vol.% triethanolamine aqueous solution using xenon light (λ >400 nm). The results on blank experiments in the absence of catalyst and light, respectively, are shown. Notably, in the blank experiments, all the other conditions remain the same. b) Photocatalytic H₂ evolution rates of HfS₂ NSs, 0.0H, and 40.0H in \approx 17 vol.% triethanolamine aqueous solution, BA aqueous solution, and benzylamine aqueous solution, respectively, using xenon light (λ >400 nm). c) High-Resolution XPS spectra of Cd 3d for 40.0H with light on and off, respectively. d) High-Resolution XPS spectra of Hf 4f for 40.0H with light on and off, respectively. e) High-Resolution XPS spectra of S 2p for 40.0H with light on and off, respectively. f) KPFM image of 40.0H in darkness. g) The corresponding line analysis of potential signal for 40.0H with light illumination along line 2 (same line; Figure 3h).

range of 250–≈550 nm and raised light absorption in the range of ≈550–800 nm, compared with 0.0H. This difference arises from the much lower light absorption in the range of 250–≈550 nm and higher light absorption in the range of ≈550–800 nm for 40.0H, compared with that of 0.0H. Thus, we need to confirm whether the enhanced light absorption in the range of ≈550–

800 nm can help raise the photocatalytic activity of 40.0H. 740nm LED instead of xenon light was utilized to test the photocatalytic H₂ evolution activity of 40.0H (Figure S15, Supporting Information). No activity was observed in the above conditions, suggesting the enhanced light absorption at \approx 550–800 nm probably imposes no effect on the activity for 40.0H.

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Then, the band structures of HfS₂ NSs and CdS (0.0H) were calculated, respectively. Figure S16a (Supporting Information) exhibits the Mott-Schottky (M-S) plot of HfS₂ NSs, suggesting its flat band potential of +0.76 V versus Ag/AgCl electrode. Thus, the Fermi level of HfS₂ NSs is +0.76 V versus Ag/AgCl electrode, corresponding to +1.36 V versus the Reversible hydrogen electrode (RHE). The XPS valence band (VB) spectrum of HfS₂ NSs is 0.41 eV (Figure S16b, Supporting Information). Thus, the VB position of HfS₂ NSs is +1.77 V versus RHE. According to the UV-vis diffuse reflectance spectrum of HfS₂ NSs (Figure S16c, Supporting Information), the bandgap of HfS₂ NSs is 1.42 eV. Thus, the CB position of HfS₂ NSs is calculated to be +0.35 V versus RHE. Thus, the CB and VB edge positions of HfS₂ NSs are shown in Figure S16d (Supporting Information). Then, we use the above same route to determine that the CB and VB edge positions of CdS (0.0H) are -1.03 and +1.19 V versus RHE, as shown in Figure S17a-d (Supporting Information). Thus, based on the band structures of HfS2 NSs and CdS, a type II (straddling type) heterojunction is formed between HfS₂ NSs and CdS in 40.0H (Figure S18, Supporting Information).

2.4. Photo-Generated Electrons/Holes Kinetics

Photo-generated electrons/holes kinetics of 40.0H were studied using various types of characterizations including transient photocurrent (TPC) density measurement, steady-state photoluminescence (PL), in situ XPS, in situ AFM-Kelvin probe force microscopy (KPFM), steady-state/transient-state surface photovoltage (SPV) spectroscopy and ultrafast transient absorption spectroscopy (TAS). The TPC density measurements of 0.0H, 40.0H, and HfS₂ NSs are shown in Figure S19 (Supporting Information). HfS₂ NSs exhibit a very small TPC density value of \approx 2.8 µA with light on, suggesting its low separation/transfer efficiency, probably arising from its intrinsic features. In comparison, bare CdS (0.0H) shows a much higher TPC density value of \approx 9.6 µA with light on, followed by gradual reduction to $\approx 6.1 \ \mu A \ cm^{-2}$ within 60 s. These results indicate the better separation/transfer efficiency of CdS (0.0H) compared to that of HfS₂ NSs. As a comparison, 40.0H shows a higher TPC density of $\approx 10.0 \ \mu A \ cm^{-2}$ with light on, accompanied with a small reduction ($\approx 1 \,\mu A \, cm^{-2}$) on TPC density in 60 s. These results confirm the key role of HfS₂ NSs on effectively reducing the electron-hole recombination for 40.0H. Then, the steady-state PL spectra (Figure S20, Supporting Information) of 40.0H show the reduced PL peak intensity at \approx 549 nm, compared with that of 0.0H at \approx 559 nm, indicating the suppressed radiative electron-hole recombination in CdS phase of 0.0H and 40.0H. Compared with 0.0H, the tiny blue shift of PL peak observed for 40.0H is attributed to the slightly-raised bandgap width of CdS NPs, arising from the higher dispersion and less aggregation of CdS NPs on HfS₂ NSs than CdS NPs alone.^[44] Furthermore, in situ, XPS were conducted with light on to provide the steady-state and element-resolved photo-generated electrons/holes separation/transfer information on 40.0H. As shown in Figure 3c-e, with light illumination, Cd 3d, Hf 4f, and S 2p peaks of 40.0H all shift to the higher binding energy direction, compared to those of 40.0H with light off. These results indicate the accumulation of more photo-generated holes than electrons on the surface of 40.0H (elements Cd, Hf, and S)

with light on. Then, in situ, AFM-Kelvin probe force microscopy (KPFM) with light illumination was performed to provide the steady-state and space-resolved photo-generated electrons/holes dissociation/migration on 40.0H. Figure S21a (Supporting Information) shows the dispersion of CdS NPs on the surface of HfS₂ NSs in darkness. This is further confirmed by the corresponding height profile (Figure S21b, Supporting Information) of 40.0H. Almost the same results (Figure S21c,d, Supporting Information) for 40.0H with light illumination are observed. The KPFM images and corresponding line analyses in the same region for 40.0H with light off and on are displayed in Figure 3fi. As displayed in Figure 3g, without light illumination, 40.0H exhibits a potential difference of \approx 40 mV between the highest potential point and the base. In contrast, a potential difference of ≈ 60 mV between the highest potential point and the base is observed for 40.0H with light illumination, suggesting the accumulation of more photo-generated holes than electrons on the surface of 40.0H with light illumination.^[45,46] Then, we utilize the transient-state/steady-state SPV spectroscopy to study the dissociation/transfer/trapping/recombination of photo-excited electrons and holes on the surface of 0.0H and 40.0H (Figure 4a,b). As displayed in Figure 4a, 0.0H first exhibits a sharp rise to the highest positive SPV signal (≈17.66 µV) at ≈0.111 µs, suggesting the transfer of much more photo-excited holes than electrons on the surface of 0.0H at \approx 0.111 µs. Then, we observe a rapid decay of the SPV positive signal to zero at $\approx 0.164 \ \mu s$, suggesting that these photo-excited holes are rapidly recombining with the photo-excited electrons transferring to the surface of 0.0H. Subsequently, the SPV signal turns into negative and reaches the largest negative signal of \approx -22.73 µV at \approx 7.424 µs, suggesting the gradual migration and accumulation of photoexcited electrons from bulk onto surface of 0.0H. The slower migration of photo-excited electrons than holes from bulk to the surface of 0.0H could be attributed to the existence of electrontrapping sites in the bulk of 0.0H. Then, we observe the gradual decay of the negative SPV signal to zero at ≈ 0.733 ms, due to the recombination of photo-excited electrons and holes on the surface of 0.0H. In contrast, after HfS₂ NSs combined with CdS NPs in 40.0H, a less steep spike is observed for 40.0H after light excitation, suggesting the slower transfer of photo-excited holes from bulk to surface. And also a lower highest SPV positive signal of $\approx 10.56 \ \mu\text{V}$ is achieved at $\approx 0.119 \ \mu\text{s}$ by 40.0H, followed by a much slower decay of the positive SPV signal to 0 at $\approx 10.62 \ \mu s$. Then, the SPV signal turns negative and reaches the largest negative potential of \approx -5.37 µV at \approx 122.79 µs. Finally, the negative SPV signal of 40.0H decays to zero at \approx 1.845 ms. These results confirm that the introduction of HfS₂ NSs significantly extends the lifetime of photo-generated holes on the surface of 40.0H. Besides, the lifetime of photo-generated electrons in 40.0H is also elongated to some extent. However, the maximum numbers of photo-generated electrons and holes on the surface of 40.0H are reduced compared to those of 0.0H, as revealed by the lower largest negative/positive potentials of 40.0H than those of 0.0H (Figure 4a). This is further confirmed by the lower steady-state SPV value of 40.0H, in contrast with that of 0.0H (Figure 4b). Besides, the absolute transient-state SPV value of 40.0H is also lower than that of 0.0H (Figure 4a). The reason is that HfS₂ NSs to some extent block the light absorption by CdS NPs in 40.0H. Furthermore, ultrafast TAS was utilized to study

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Figure 4. a) Transient-state SPV spectra of 0.0H and 40.0H. b) steady-state SPV spectra of 0.0H and 40.0H. 2D pseudo-color TA spectra of c) 0.0H and d) 40.0H after the excitation with a 400 nm laser pulse. e) Normalized decay kinetics and fitting lines for 0.0H and 40.0H taken through the GSB peaks at \approx 505 nm.

the photo-generated charge carrier kinetics in 40.0H. As shown in Figure 4c,d, 2D pseudo-color TA spectra shows an obvious negative absorption in the range of \approx 450– \approx 580 nm, attributed to the ground state bleaching (GSB) signal.^[47,48] The normalized decay kinetics and corresponding fitting at 505 nm for 0.0H and 40.0H (Figure 4e) further demonstrate the slower decay of GSB signal for 40.0H, compared with that of 0.0H. Since GSB signal at 505 nm is directly related with the photo-excited holes in the VB of CdS phase in 0.0H and 40.0H, the slower decay kinetics of GSB signal indicates the longer lifetimes of photo-excited holes in CdS phase of 40.0H, in contrast with those of 0.0H. These results are in accordance with the above TPC density measurement (Figure S19, Supporting Information) and transient-state SPV results (Figure 4a). Therefore, according to the above results on TPC density measurement, steady-state PL, in situ XPS, in situ AFM-KPFM, steady-state/transient-state SPV, and ultrafast

TAS, we can conclude several things below: i) with HfS_2 NSs introduced in 40.0H, more photo-generated holes than electrons are driven to the surface of 40.0H with light illumination; ii) the lifetimes of both photo-generated electrons and holes (especially the hole lifetime) for 40.0H are elongated compared to those for 0.0H; iii) the maximum numbers of photo-generated electrons and holes on the surface of 40.0H are reduced to some extent, in contrast with those of 0.0H.

2.5. Surface Redox Reactions and Photocatalytic Mechanism

Finally, we studied the surface redox reactions on 40.0H, which are H_2 evolution and BA oxidation reactions, respectively. As displayed in Figure S22 (Supporting Information), after introducing HfS₂ NSs, no obvious change on the overpotential for H_2

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evolution is observed for 40.0H, compared to that of 0.0H. These results suggest that HfS₂ NS is not an excellent H₂ evolution catalysts. Thus, HfS₂ NSs in 40.0H don't serve as the co-catalyst like Pt or MoS₂ reported in the references. Instead, HfS₂ NSs could function as the key component in type II hetero-junction (Figure S18, Supporting Information) to raise the photocatalytic performance of 40.0H. For the BA oxidation reaction, the 12 h BA conversion (54.61%) and BAD selectivity (20.04%) for 40.0H are obviously higher than those of 0.0H (BA conversion: 49.70%; BAD selectivity: 14.31%) as shown in Figure S13a,b (Supporting Information). These results indicate that the introduction of HfS₂ NSs not only raises the oxidative conversion of BA, but also increases the selectivity of BA-to-BAD transformation. Based on the above results, the photocatalytic mechanisms of H₂ and BAD evolution on 40.0H is raised in Figure S23 (Supporting Information). With light illumination, photo-excited electrons and holes are generated in the CB and VB of CdS and HfS₂, respectively. Then, since CdS and HfS₂ are combined together to form the type II heterojunction, the photo-generated electrons are transferred from the CB of CdS to the CB of HfS₂ for H₂ evolution; whilst the photo-generated holes are transferred from the VB of HfS₂ to the VB of CdS for the oxidation of BA to form BAD. This type II heterojunction raises the efficiency of photo-generated electron/hole dissociation/transfer in 40.0H, compared to 0.0H. Besides, due to the existence of atomic-level S vacancies in HfS₂ NSs, the photo-generated electrons transferred to the CB of HfS₂ NSs are temporarily trapped by the atomic-level S vacancies, thus retarding the recombination of electrons with holes in HfS₂ NSs. Then, these photo-generated electrons will be released to reduce protons and forming H₂ gas. Thus, these atomic-scale S vacancies in HfS₂ NSs further raise the photocatalytic performance of 40.0H via

realizing the spatiotemporal separation of electrons and holes. Thus, the roles of HfS_2 NS in 40.0H are summarized as follows: i) it serves as the platform to boost the general dispersion and intimate contact of CdS NPs; ii) the formation of type II heterojunction between HfS_2 NSs and CdS NPs boosts the efficient charge separation/transfer; iii) the atomic-scale S vacancies in HfS_2 NSs function as the electron trap to reduce the electron–hole recombination.

2.6. HfS₂ NSs Raising Activities on ZnIn₂S₄, C₃N₄, and TiO₂

To confirm that HfS_2 NSs can raise the photocatalytic H_2 evolution of various photocatalysts, we have for the first time synthesized a range of HfS_2 -based photocatalysts including HfS_2 -TiO₂, HfS_2 -ZnIn₂S₄, and HfS_2 -C₃N₄ using the similar method for fabricating 40.0H. They are labeled as $40HfS_2$ -TiO₂, $40HfS_2$ -ZnIn₂S₄, and $40HfS_2$ -C₃N₄, respectively. The XRD patterns of TiO₂, $40HfS_2$ -TiO₂, $ZnIn_2S_4$, $40HfS_2$ -ZnIn₂S₄, C_3N_4 and $40HfS_2$ -C₃N₄ are displayed in **Figure 5**a-c. Several new peaks ascribed to HfS_2 are observed for $40HfS_2$ -TiO₂, $40HfS_2$ -ZnIn₂S₄, and $40HfS_2$ -C₃N₄, confirming the successful combination of HfS_2 NSs with TiO₂, ZnIn₂S₄, and C₃N₄, respectively. Besides, no apparent change for the positions and intensities of diffraction peaks for TiO₂ in $40HfS_2$ -C₃N₄ are observed, compared to TiO₂, ZnIn₂S₄, and C₃N₄ in $40HfS_2$ -C₃N₄, respectively. Furthermore, the TEM images

(Figure S24a,c,e, Supporting Information) and the corresponding EDX spectra (Figure S24b,d,f, Supporting Information) of 40HfS₂-TiO₂, 40HfS₂-ZnIn₂S₄, and 40HfS₂-C₃N₄ further corroborate the coupling of HfS₂ NSs with TiO₂, ZnIn₂S₄, and C₃N₄, respectively. Then, the photocatalytic H₂ evolution of 40HfS₂-TiO₂, 40HfS₂-ZnIn₂S₄, and 40HfS₂-C₃N₄ were tested in \approx 17 vol.% triethanolamine aqueous solution using xenon light. As shown in Figure 5d, compared with TiO₂, ZnIn₂S₄ or C₃N₄ alone, 40HfS₂-TiO₂, 40HfS₂-ZnIn₂S₄, or 40HfS₂-C₃N₄ exhibit the apparentlyraised photocatalytic H₂ evolution rates, suggesting that HfS₂ NSs can raise the H₂ evolution of these photocatalysts. These results further confirm that HfS₂ NSs can serve as an excellent platform to universally raise the photocatalytic H₂ evolution on various photocatalysts. To investigate the reasons on the raised photocatalytic efficiency, both the light absorption properties and charge recombination of these photocatalysts were studied. First, UV-vis diffuse reflectance spectroscopy was adopted to study the light-harvesting abilities of the as-synthesized photocatalysts. As displayed in Figure S25a-c (Supporting Information), obviously raised light absorption in the range of \approx 500–800 nm was observed for 40HfS₂-TiO₂, 40HfS₂-ZnIn₂S₄, and 40HfS₂-C₃N₄, due to the existence of HfS2 NSs. Furthermore, steady-state PL spectra (Figure S26a-c, Supporting Information) indicate the reduced steady-state PL intensities of 40HfS2-TiO2, 40HfS2-ZnIn2S4, and 40HfS₂-C₃N₄, compared with those of TiO₂, ZnIn₂S₄, and C₃N₄, respectively. These results indicate the impeded charge recombination in 40HfS₂-TiO₂, 40HfS₂-ZnIn₂S₄, and 40HfS₂-C₃N₄ due to the introduction of HfS2 NSs. The above results on TEM images, steady-state PL spectra, and photocatalytic activities together confirm the successful establishment of effective and intimate junction between HfS₂ NSs with TiO₂, $ZnIn_2S_4$, and C_3N_4 , respectively. These effective junctions in 40HfS₂-TiO₂, 40HfS₂-ZnIn₂S₄, and 40HfS₂-C₃N₄ also enable that HfS₂ NSs could serve as a universal platform to significantly raise the photocatalytic activities. Especially, the atomic-scale S vacancies in HfS₂ NSs work as the electron trap to boost the electron-hole separation/transfer.

3. Conclusion

In conclusion, we fabricated the novel HfS₂ nanosheets (NSs) with atomic-scale S vacancies via the sonication route. Thus, the as-synthesized HfS₂ NSs were combined with different photocatalysts to acquire the new HfS2-TiO2, HfS2-CdS, HfS2-ZnIn2S4, and HfS₂-C₃N₄ composite photocatalysts, respectively. Among them, optimized HfS₂-CdS composite displays the largest photocatalytic H₂ evolution rate (5971 μ mol g⁻¹ h⁻¹) in triethanolamine aqueous solution, together with evidently raised generation activities of H_2 (2419 µmol g⁻¹ h⁻¹) and benzaldehyde (5.11 mmol g^{-1} h⁻¹) than bare CdS in benzyl alcohol aqueous solution. Advanced characterizations, such as in situ X-ray photoelectron spectroscopy (XPS), in situ atomic force microscopy-Kelvin probe force microscopy (AFM-KPFM) and ultrafast transient absorption spectroscopy (TAS), together reveal that the numerous atomic-level S vacancies in HfS2 NSs function as the trapping centers to temporarily host the electrons, thus significantly boosting the electron-hole separation/transfer in 40.0H. Our work not only demonstrates the significance of atomic-scale regulation on new 2D materials for photocatalysis application, but also

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Figure 5. XRD patterns of a) TiO₂ and 40HfS₂-TiO₂, b) ZnIn₂S₄, and 40HfS₂-ZnIn₂S₄, c) C_3N_4 and 40HfS₂- C_3N_4 , and d) Photocatalytic H₂ evolution rates of C_3N_4 , 40HfS₂- C_3N_4 , TiO₂, 40HfS₂-TiO₂, ZnIn₂S₄ and 40HfS₂-ZnIn₂S₄ in \approx 17 vol.% triethanolamine aqueous solution.

highlights the importance of using state-of-art characterizations to investigate the elements/space/time-resolved electrons/holes dynamics of photocatalysts.

4. Experimental Section

Experimental details can be found in the Supporting Information.

Supporting Information

Supporting Information is available from the Wiley Online Library or from the author.

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Conflict of Interest

The authors declare no conflict of interest.

Data Availability Statement

The data that support the findings of this study are available from the corresponding author upon reasonable request.

Keywords

atomic-scale vacancies, element/space/time-resolved charge kinetics, ${\rm HfS}_2$ nanosheets, in situ characterizations

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